ERRATA

Erratum: “Silicon Photodiode with a Grid p - n Junction” [*Semiconductors* 41, 223–226 (2007)]

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On pages 224 and 225 Figs. 2 and 4 should be as follows:

Fig. 2. Spectral-sensitivity characteristic of the grid-structured photodiode at various cell sizes h_n (dashed curve corresponds to the continuous photodiode) at hole diffusion lengths of (a) 30 and (b) 100 μm .

Fig. 4. Spectral-sensitivity characteristics of the continuous (dotted curve) and grid photodiodes with cell sizes of 50 and 110 μm .